



image

2826
AF

GR 98 P 1379 D

BOX AF

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450:

By: Wim Stu

Date: January 20, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/885,553 Confirmation No. 6319

Applicant : Lars-Peter Heineck et al.

Filed : June 20, 2001

TC/A.U. : 2826

Examiner : Johannes P. Mondt

Title: : MOS Transistor in a Single-Transistor Memory Cell Having a Locally Thickened Gate Oxide

Docket No. : GR 98 P 1379 D

Customer No. : 24131

BOX AF

Hon. Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT under 37 C.F.R. § 1.116

Sir :

In response to the final Office action dated October 22, 2003,
please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Argum nts begin on page 5 of this paper.